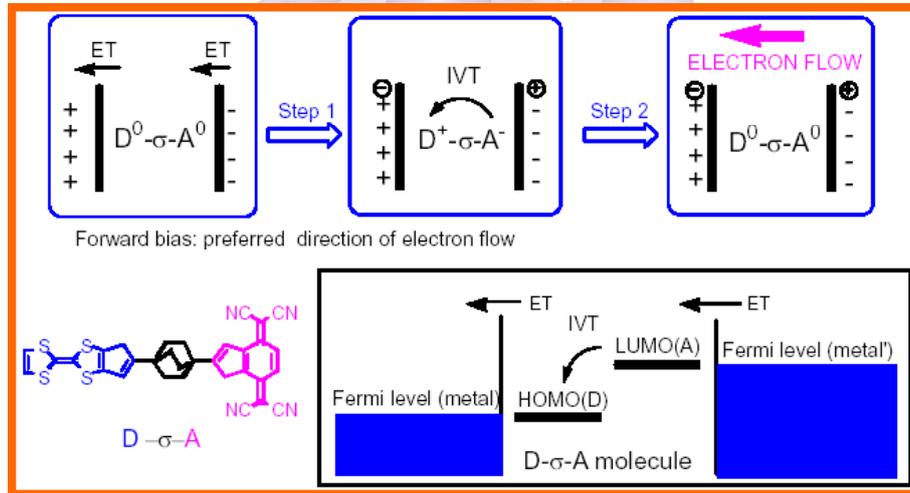
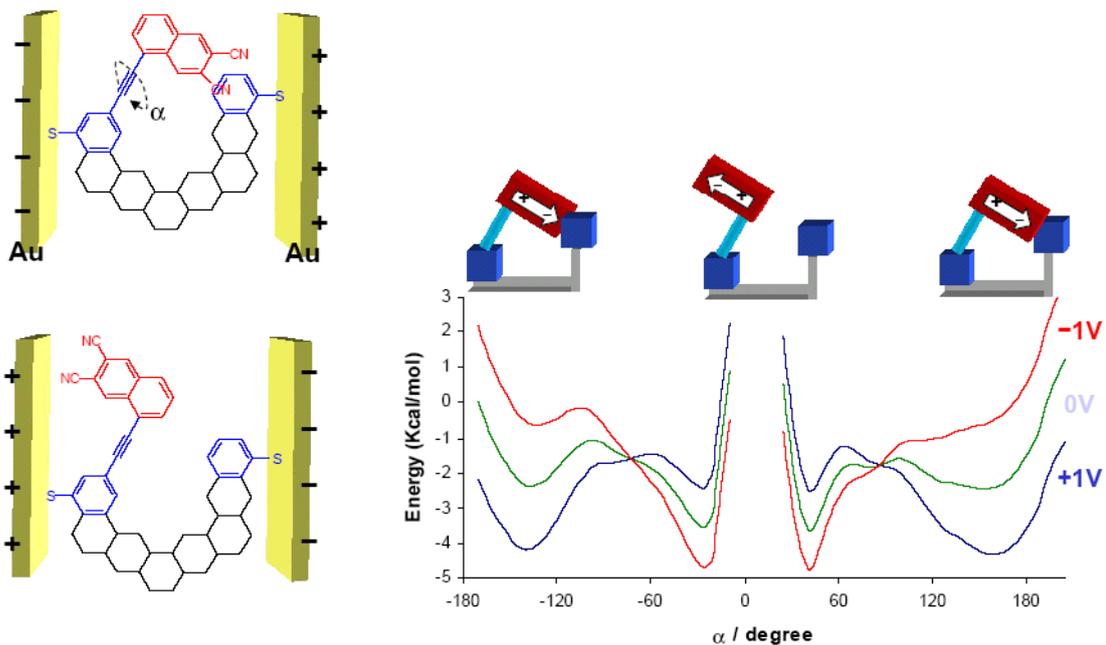


Seeing the future-A proposal ahead of time

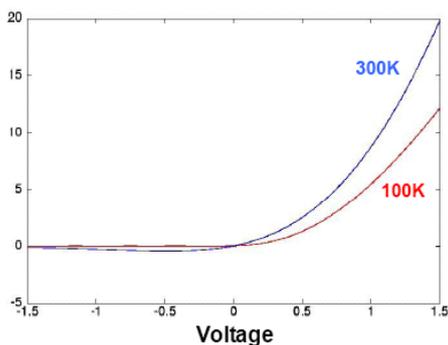
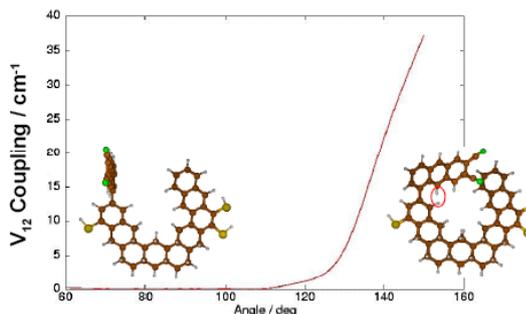
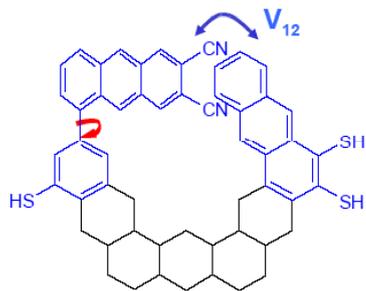


A. Aviram & M.A. Ratner (1974)

A rectifier based on *intra*-molecular structural changes (a device minimally dependent on the metal-molecule contact)



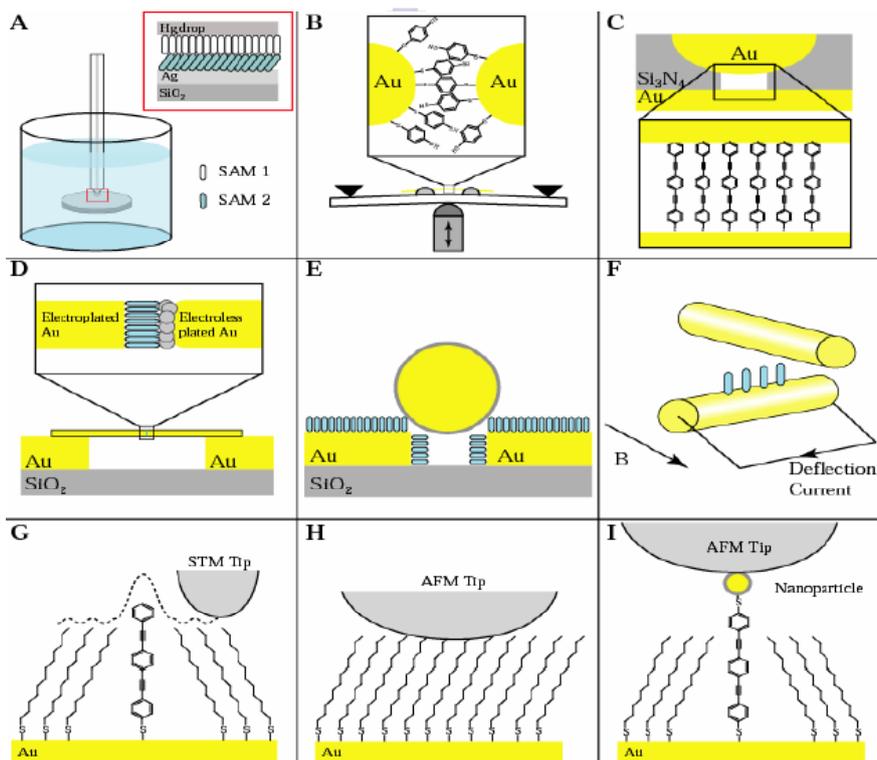
A SYSTEM WITH ONLY ONE THROUGH-SPACE COUPLING AND VERY HIGH ON/OFF CONDUCTANCE RATIO



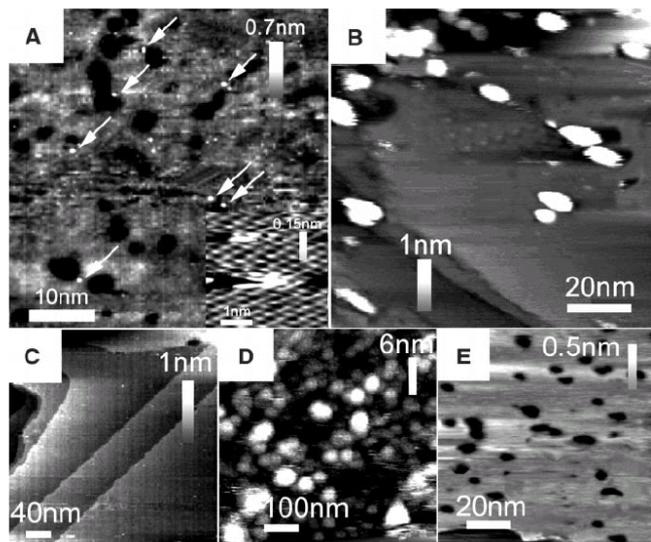
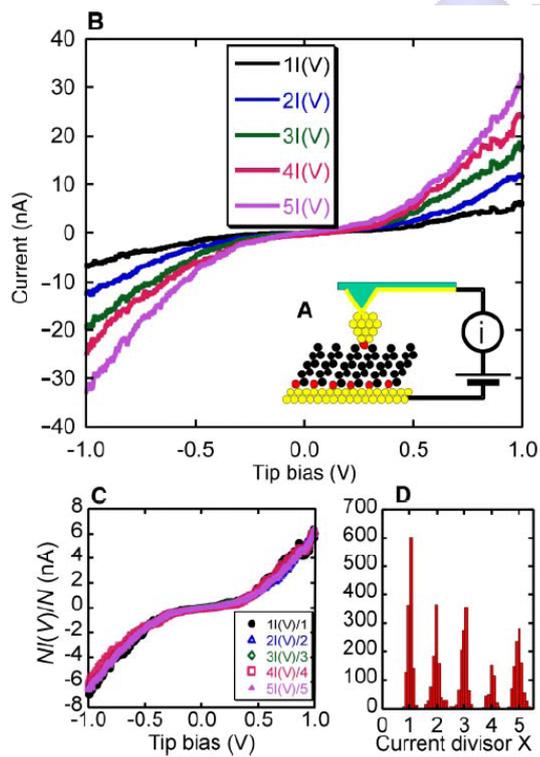
Giant Rectification/switch,
With two electrodes
From control of
stereochemistry

Troisi and MR, 2003

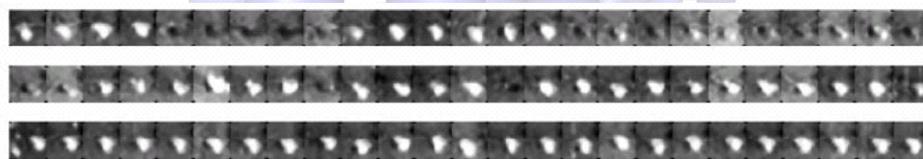
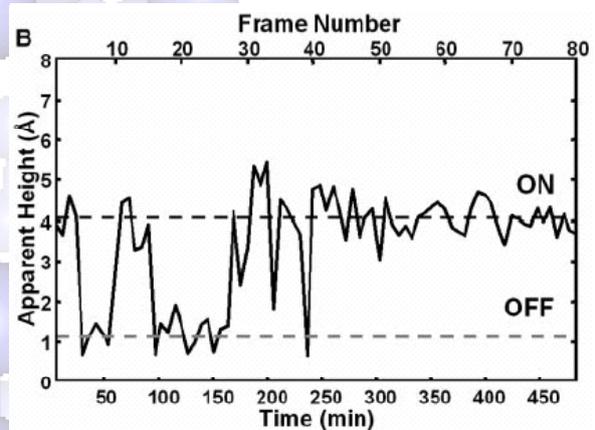
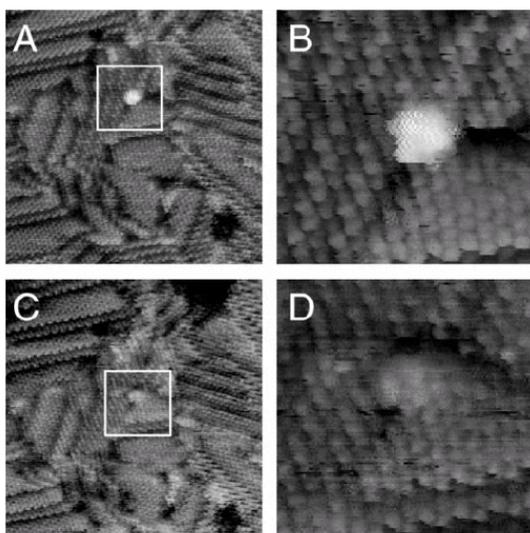
Cutting Edge Technologies in measuring small molecules



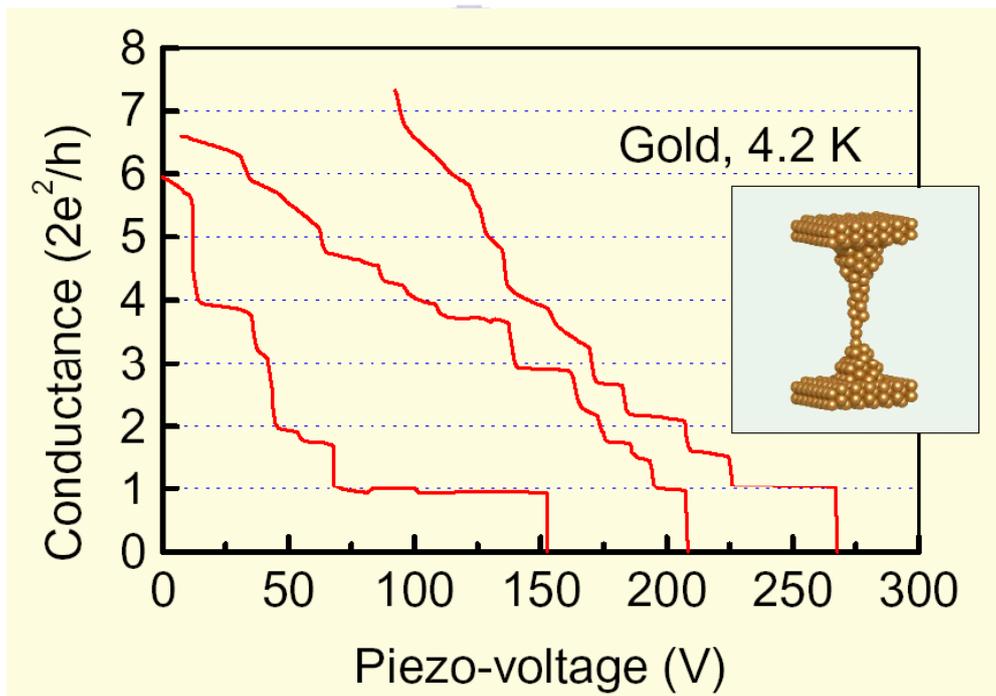
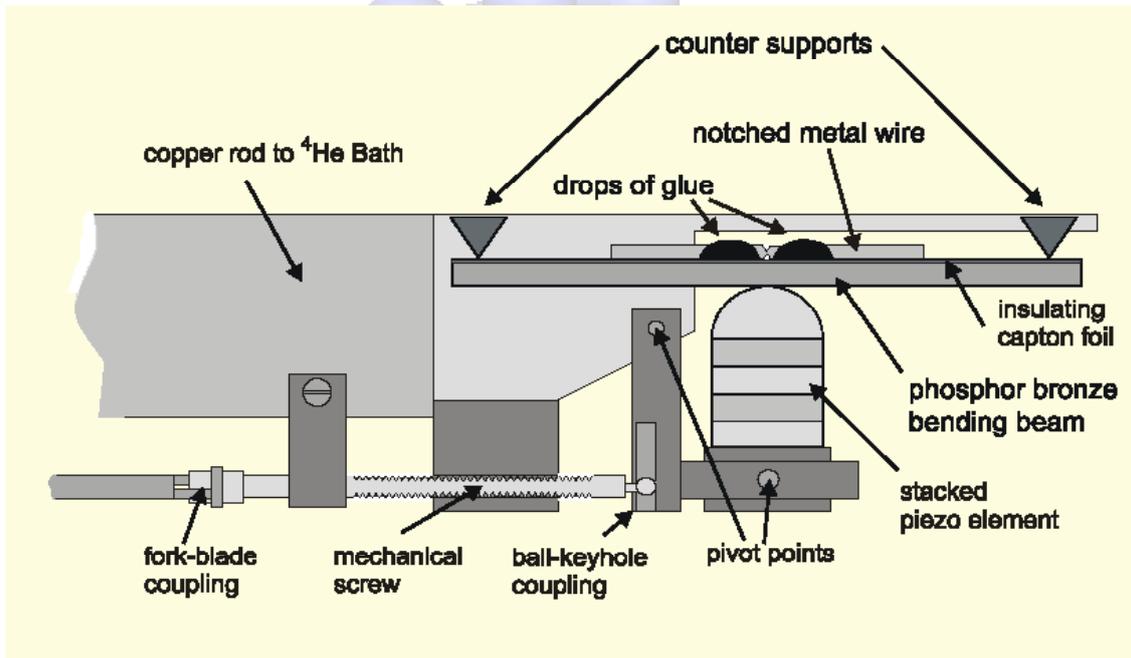
Contact dependence of the molecules (I)



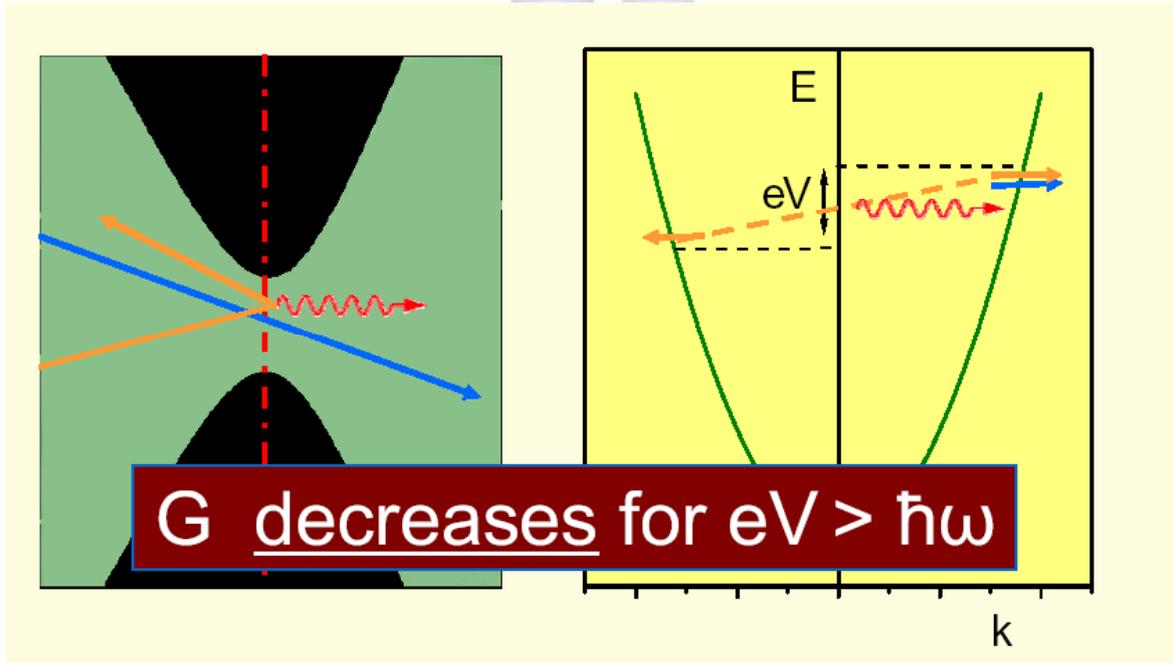
Conductance switching in single molecule (G)



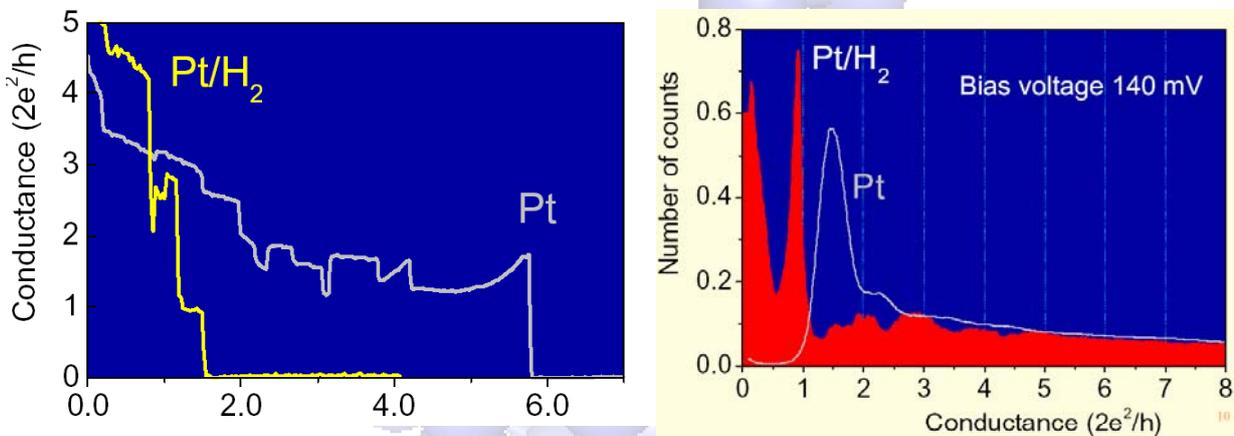
Mechanically controllable break junction (B)



Point contact spectroscopy

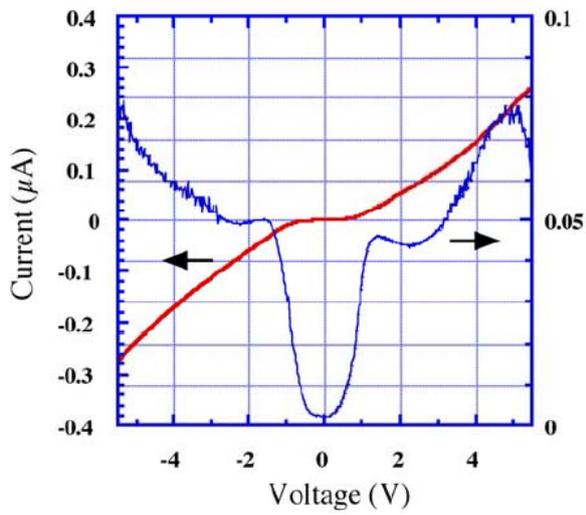


Conductance from H_2 molecule

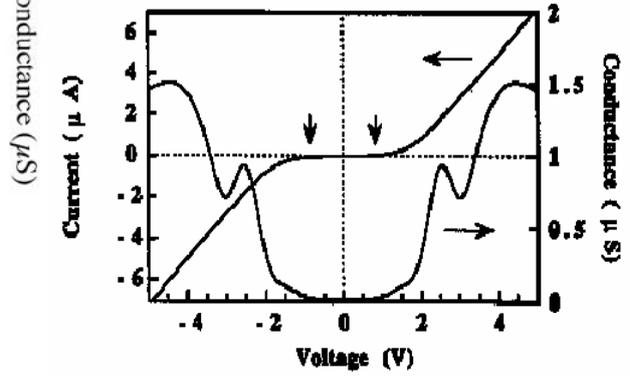
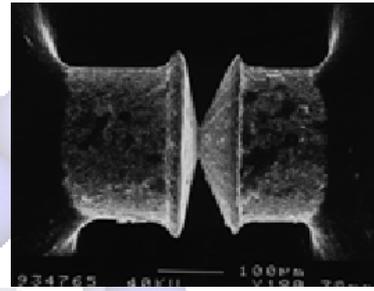


Jan van Reutenbeck, 2002

MBJ with 1-4 benzenethiol

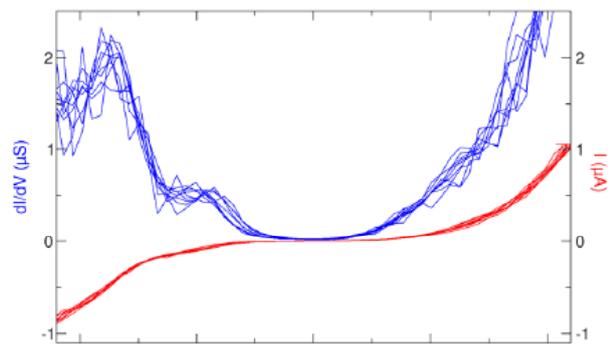
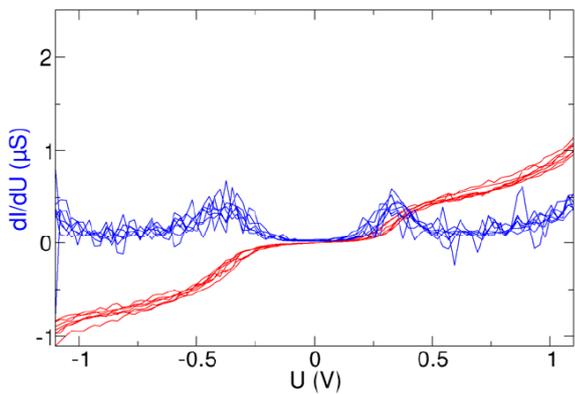
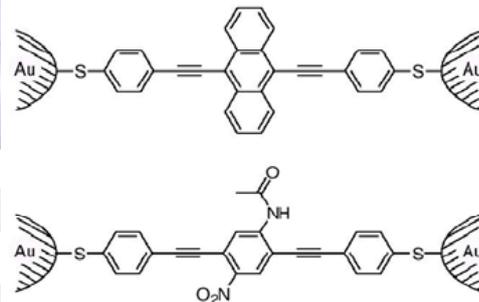
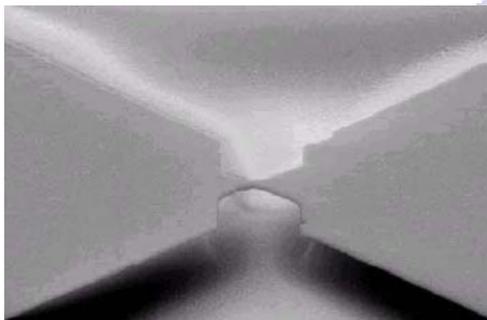


Reed et al., Science 278, 252



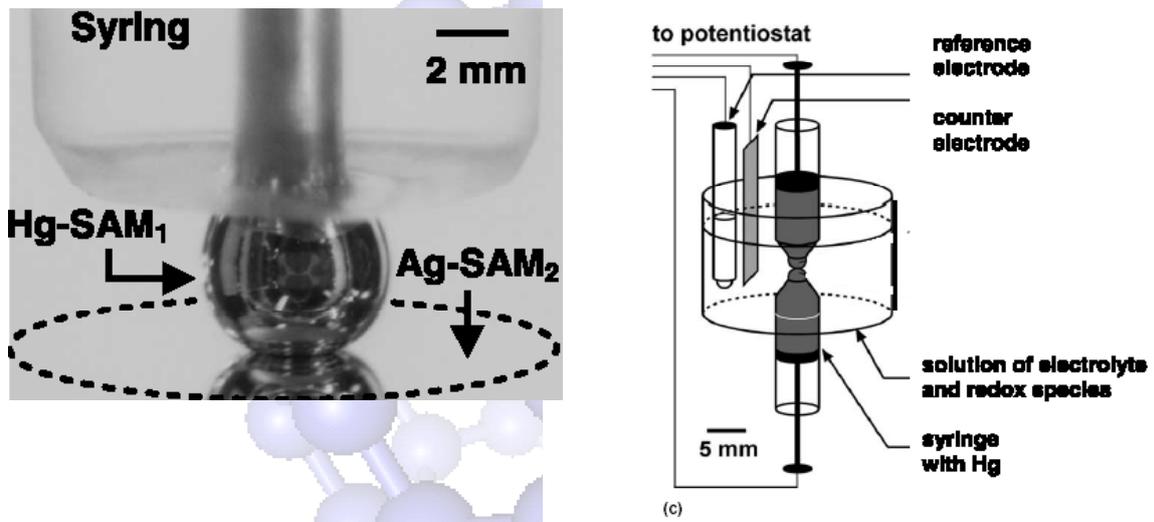
Di Ventra et al., PRL 84, 979

Metallic breakjunction measurement

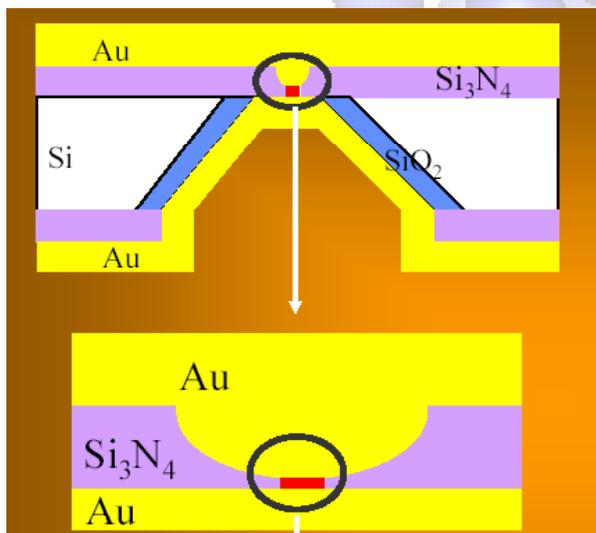


Reichert et al., PRL 88, 87604

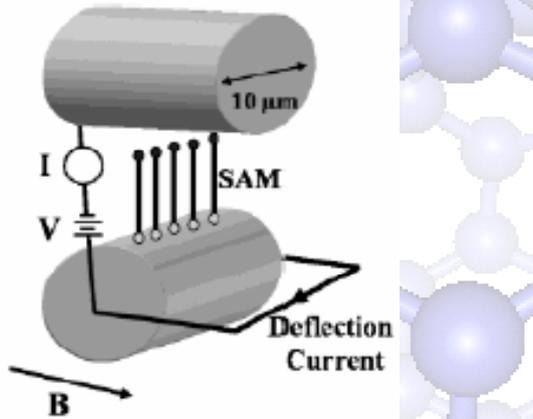
Mercury Junction



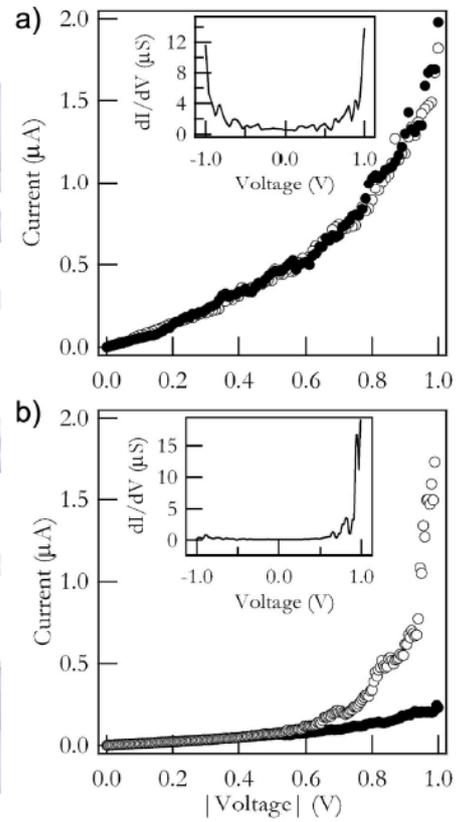
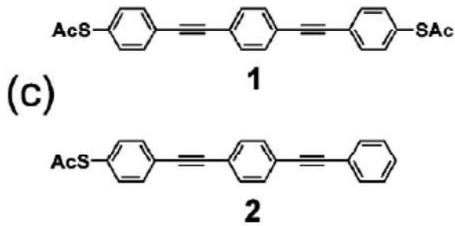
Nanopore measurement (c)



Cross wire junctions (F)

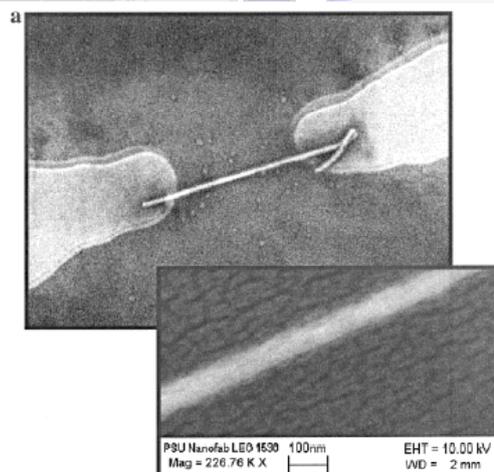
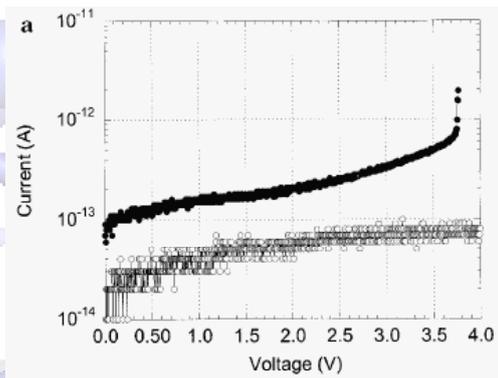
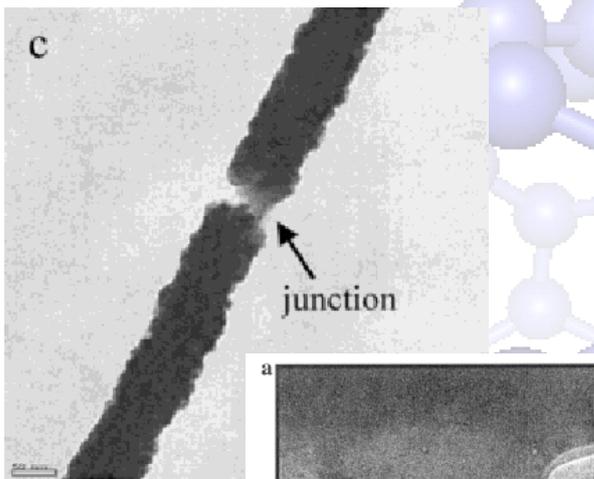


Kushmerick et al., 2002



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Nano Materials Research Team

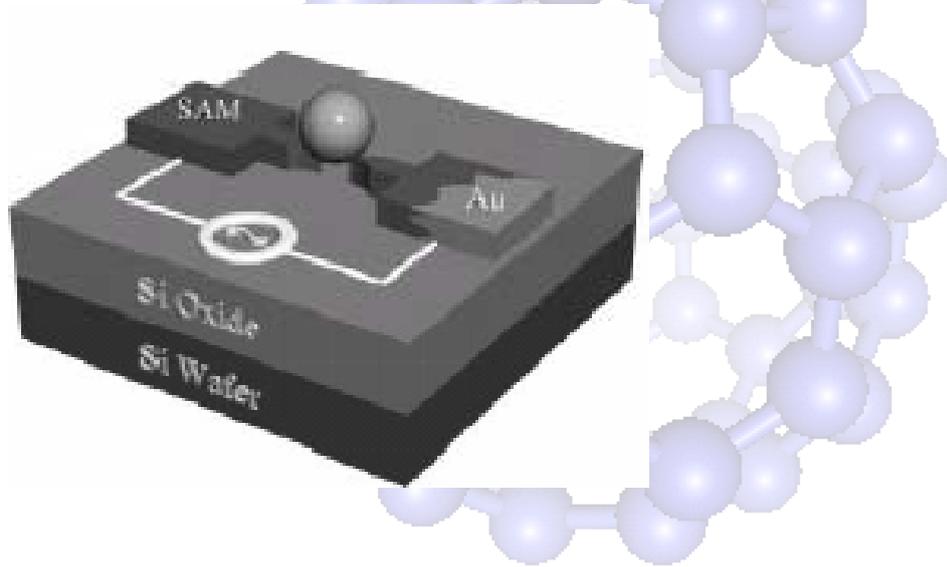
Nanowire junction (D)



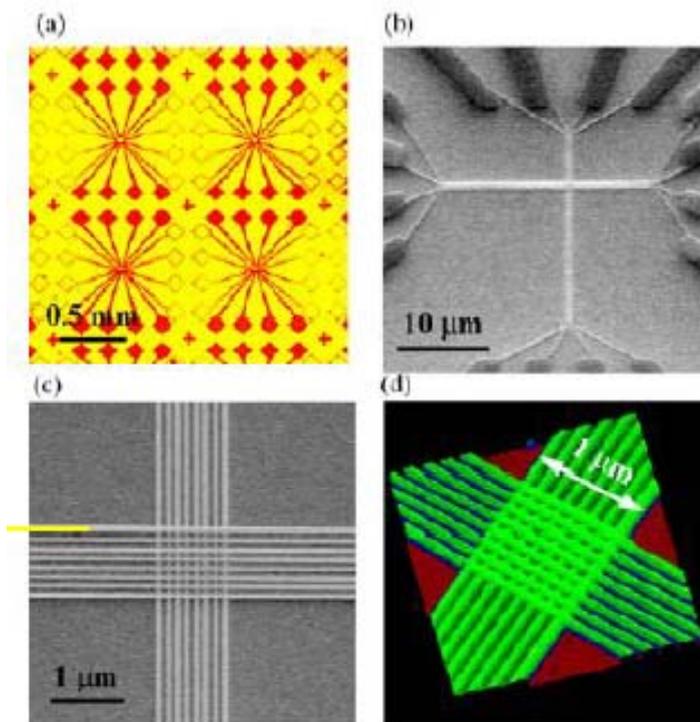
나노물성연구팀
Nano Materials Research Team

PSU Nanofab LE0 1630 100nm EHT = 10.00 kV
Mag = 226.76 K X WD = 2 mm

Nanoparticle trapped junction

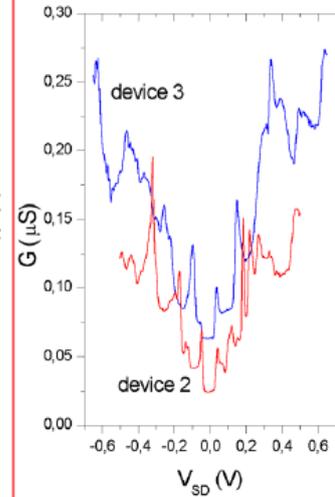
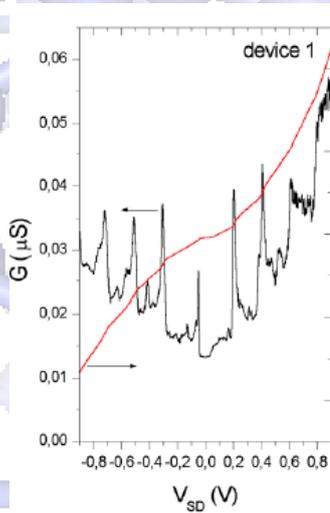
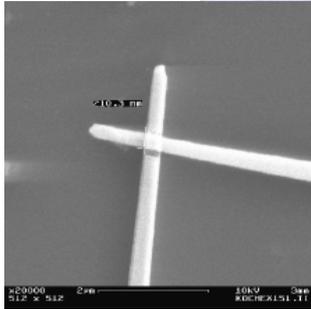
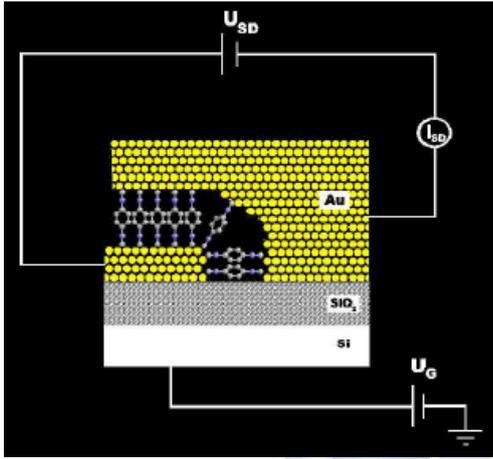


Nanowire cross junction (G)



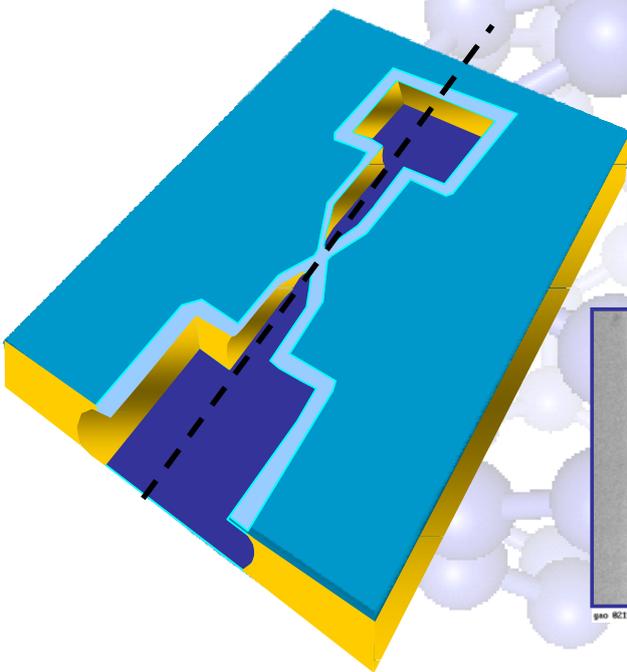
Y. Chen et al. 2003

Sandwich junction-Planar

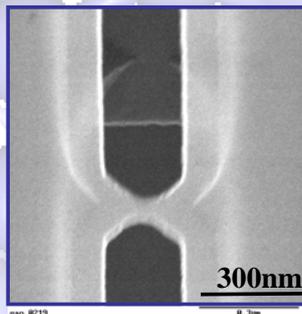


C. Dupraz et al., 2003

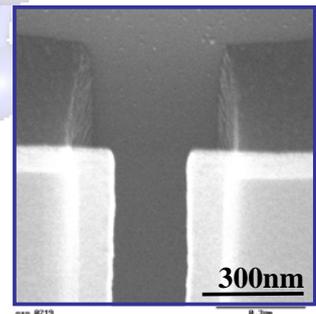
Sandwich junction-Planar



- Resist bridge that can stand the growth of the molecules
- Without lift-off process
- Controllable contact area

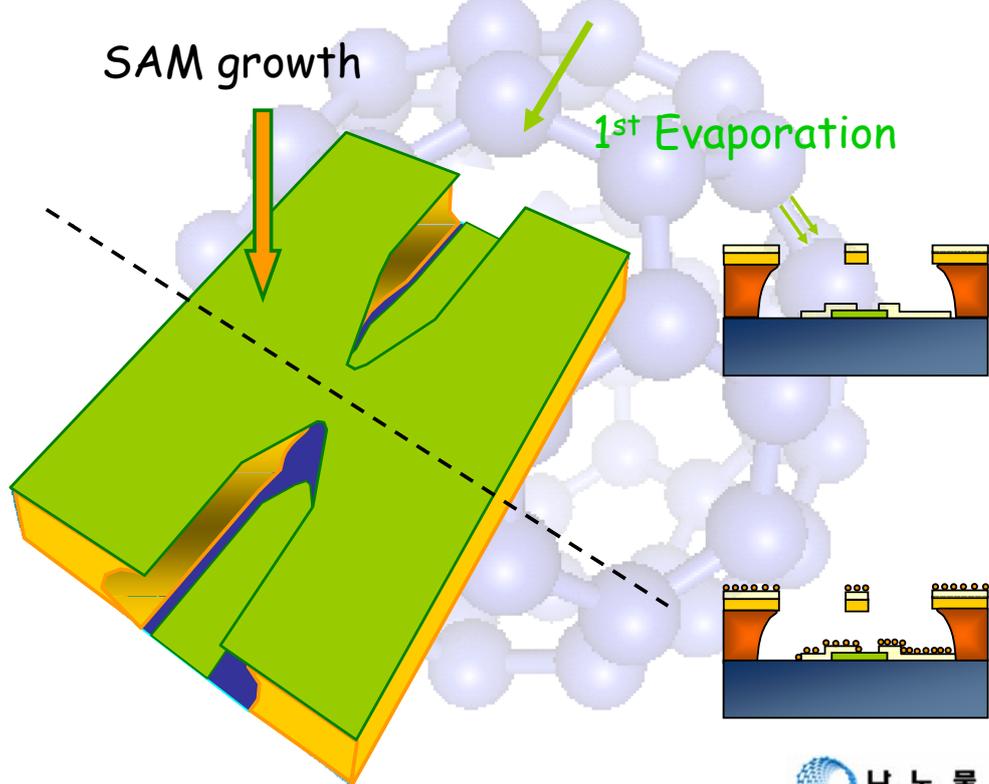


Tilted 45°

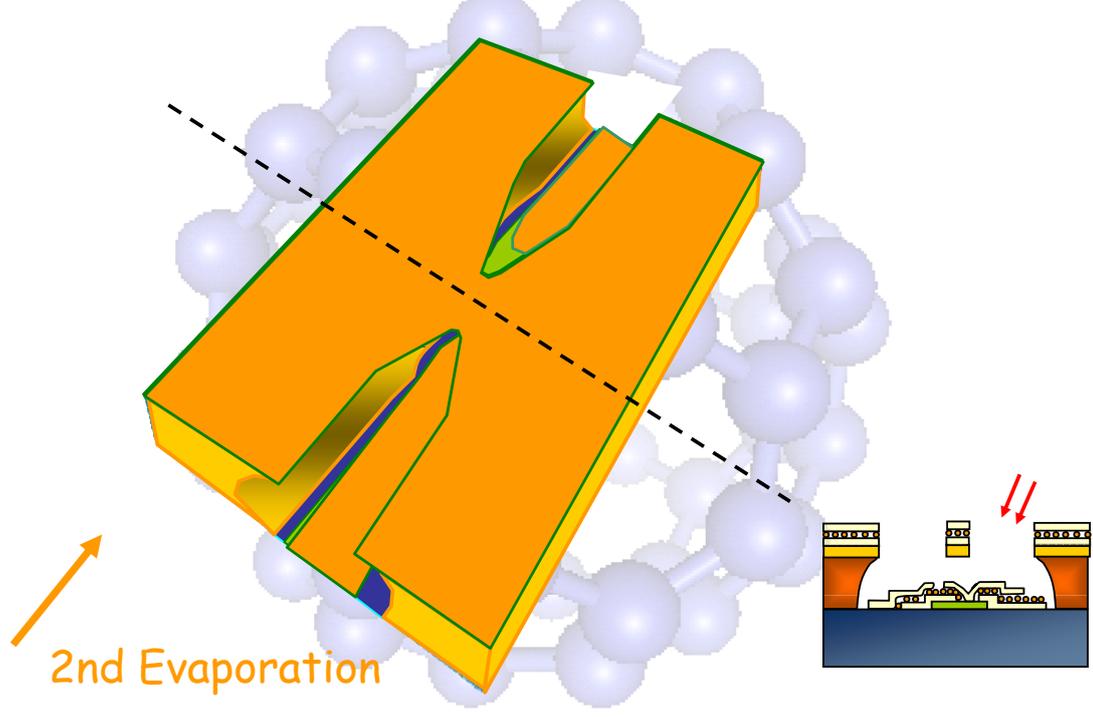


Tilted 45°

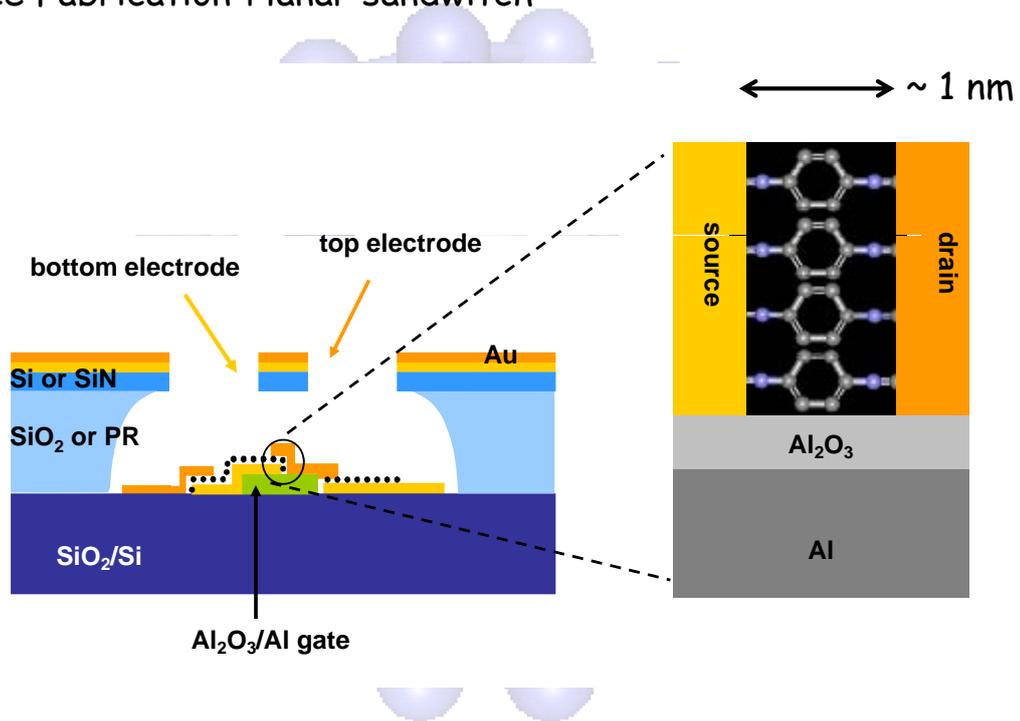
Device Fabrication-Planar sandwich



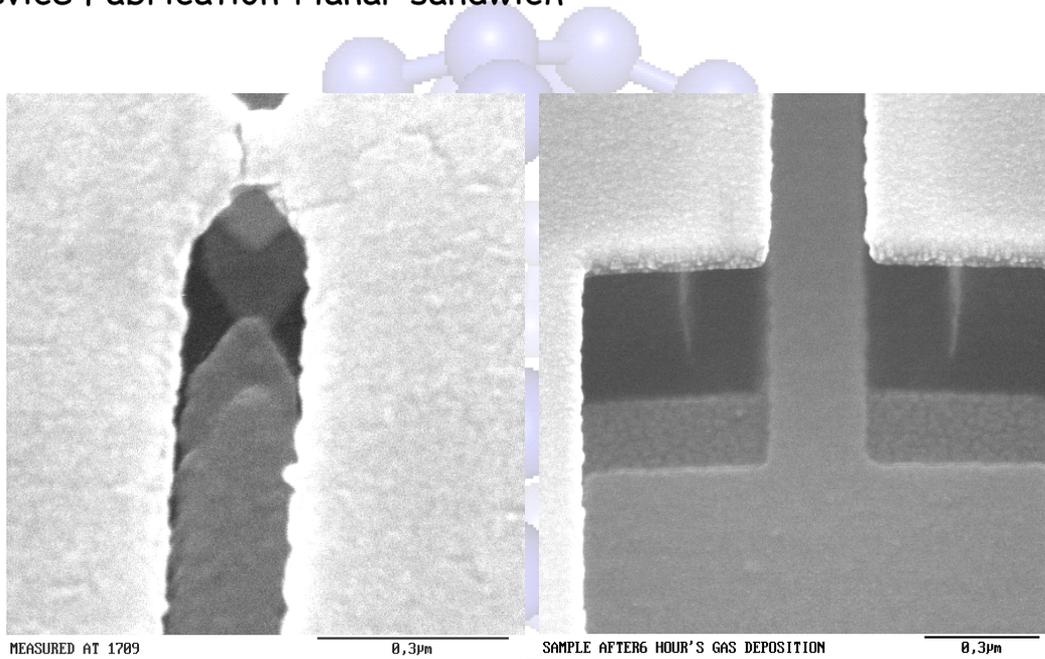
Device Fabrication-Planar sandwich



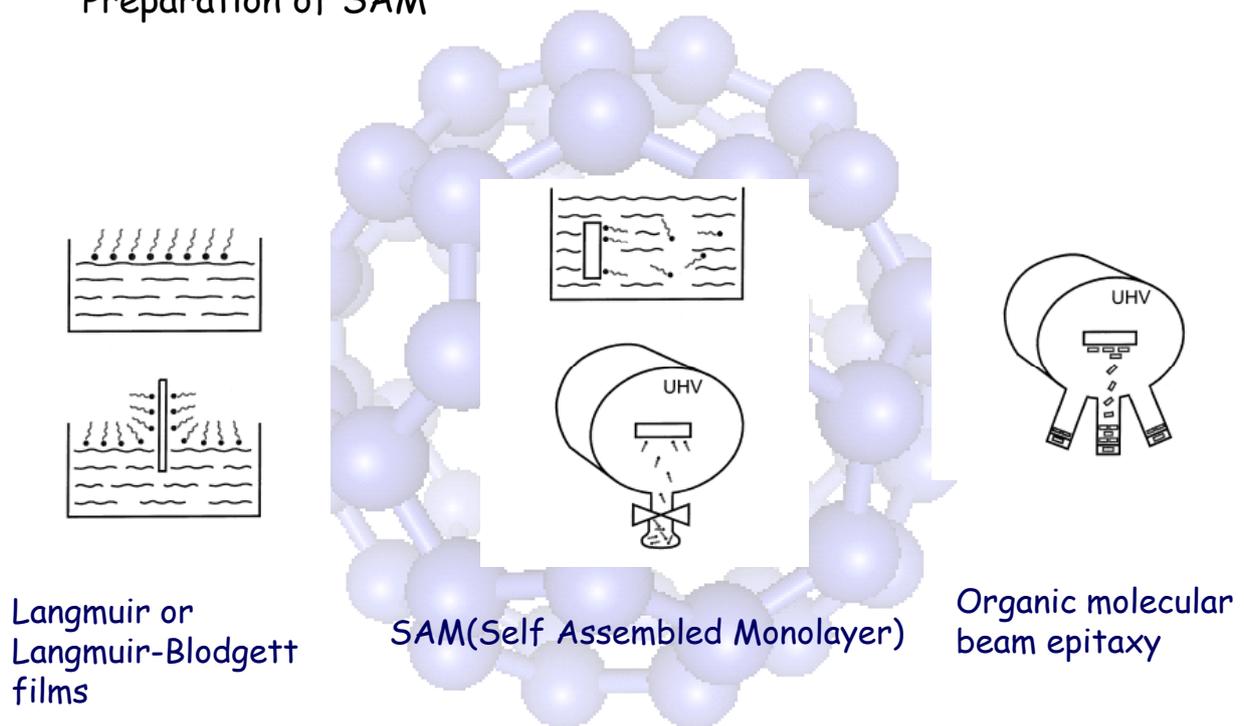
Device Fabrication-Planar sandwich



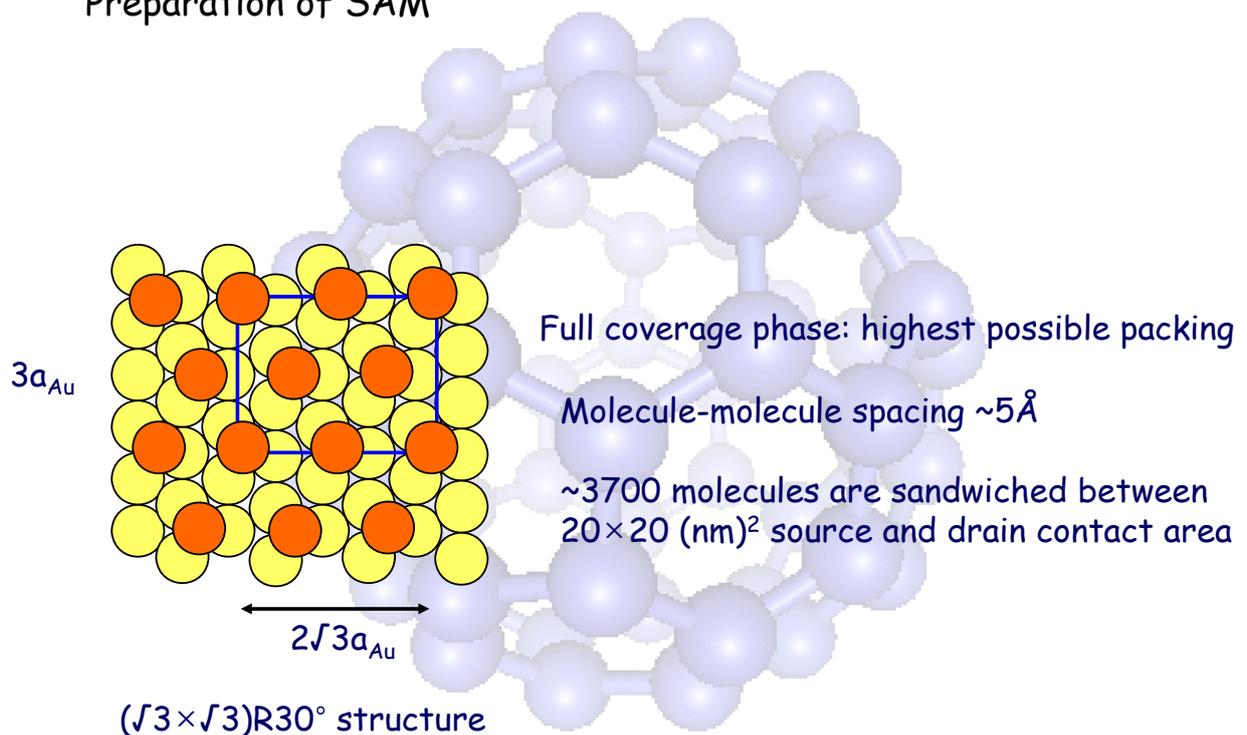
Device Fabrication-Planar sandwich



Preparation of SAM



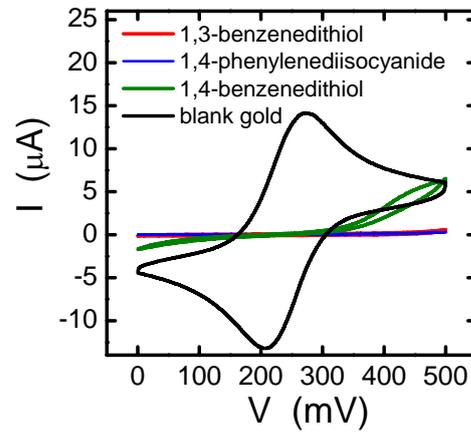
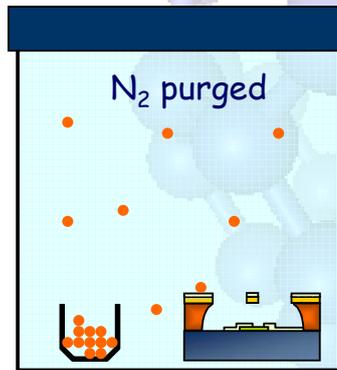
Preparation of SAM



Growth of a self-assembled monolayer of molecules

Gas phase deposition

Electrochemical testing of the monolayer



Molecules	Yield (%)	Total # of fabricated samples	Gate dependent samples	Liquid growth	Gas phase SAM growth	characteristics
1 <chem>SC1=CC=C(S)C=C1</chem>	7.8	256	2	Y	Y	Asymmetric $I-V$
2 <chem>SC1=CC=C(C=C1)S</chem>	0	216	0	Y	Y	
3 <chem>N#CC1=CC=C(C=C1)C#N</chem>	16	236	0	Y	Y	NDC
4 <chem>SC1=CC=C(C=C1)-c2ccc(S)cc2</chem>	5	108	0	Y	N	NDC
5 <chem>N#CC1=CC=C(C=C1)C#CC#CC2=CC=C(C=C2)C#N</chem>	0	72	0	Y	N	